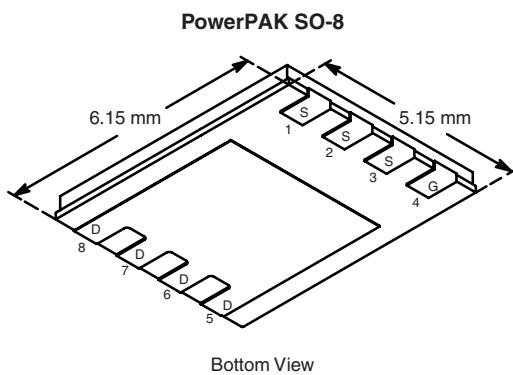


N-Channel Reduced Q_g , Fast Switching MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
30	0.007 at $V_{GS} = 10$ V	19	11.5
	0.0095 at $V_{GS} = 4.5$ V	17	

FEATURES

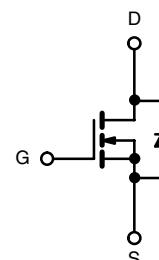
- Halogen-free available
- TrenchFET® Gen II Power MOSFET
- PWM Optimized for High Efficiency
- New Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile
- 100 % R_g Tested



Ordering Information: Si7386DP-T1-E3 (Lead (Pb)-free)
Si7386DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

- DC/DC Conversion for PC



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	30	12	V
Gate-Source Voltage	V_{GS}			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D ($T_A = 25$ °C)	19	12	A
	I_D ($T_A = 70$ °C)	16	9	
Pulsed Drain Current	I_{DM}	± 50		A
Continuous Source Current (Diode Conduction) ^a	I_S	4.1	1.5	
Avalanche Current	I_{AS}	25		mJ
Single Pulse Avalanche Energy	E_{AS}	32		
Maximum Power Dissipation ^a	P_D ($T_A = 25$ °C)	5	1.8	W
	P_D ($T_A = 70$ °C)	3.2	1.1	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}		260		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) ^a	$t \leq 10$ s	R_{thJA}	21	°C/W
	Steady State		56	
Maximum Junction-to-Case (Drain)	R_{thJC}	2.4	3.0	

Notes:

- Surface Mounted on 1" x 1" FR4 board.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

MOSFET SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

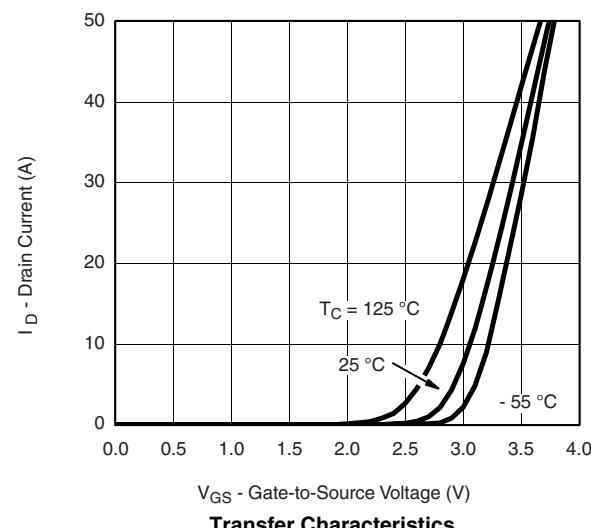
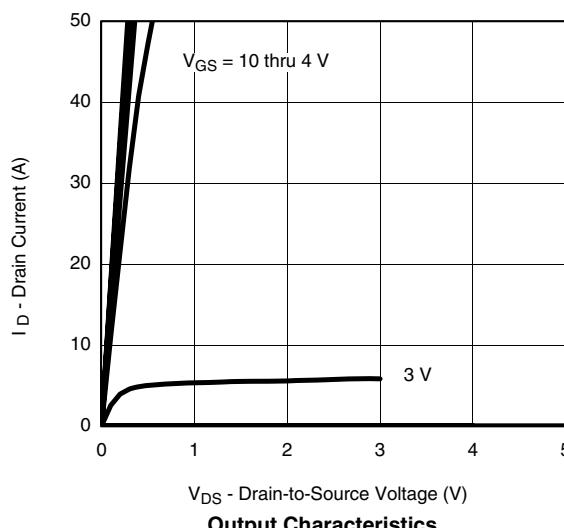
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	1.5	2.0	2.5	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$		1		μA
		$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 70^\circ\text{C}$		15		
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$, $V_{GS} = 10 \text{ V}$	40			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 19 \text{ A}$		0.0058	0.007	Ω
		$V_{GS} = 4.5 \text{ V}$, $I_D = 17 \text{ A}$		0.0078	0.0095	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 19 \text{ A}$		50		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 4.1 \text{ A}$, $V_{GS} = 0 \text{ V}$		0.78	1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}$, $V_{GS} = 4.5 \text{ V}$, $I_D = 19 \text{ A}$		11.5	18	nC
Gate-Source Charge	Q_{gs}			5.8		
Gate-Drain Charge	Q_{gd}			3.0		
Gate Resistance	R_g		0.8	1.7	2.5	Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 15 \text{ V}$, $R_L = 15 \Omega$ $I_D \geq 1 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 6 \Omega$		12	18	ns
Rise Time	t_r			9	14	
Turn-Off Delay Time	$t_{d(\text{off})}$			35	53	
Fall Time	t_f			10	15	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.8 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$		25	50	

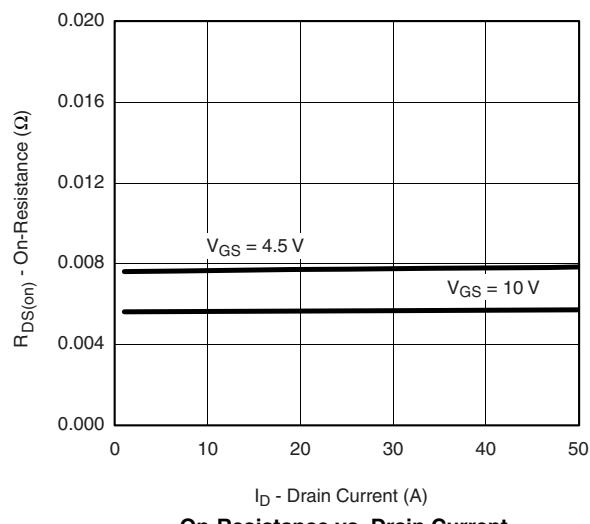
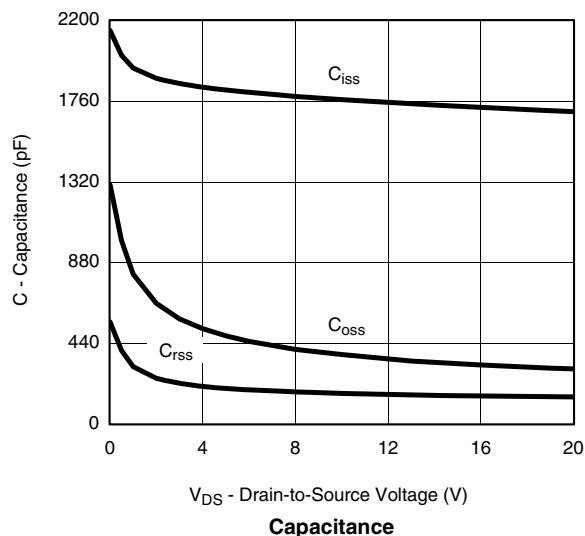
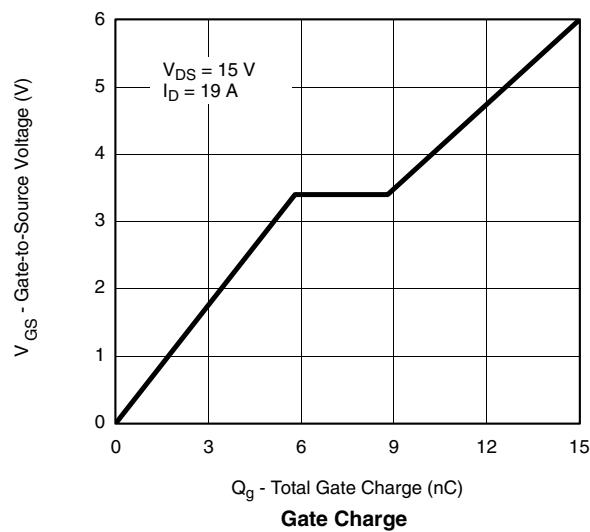
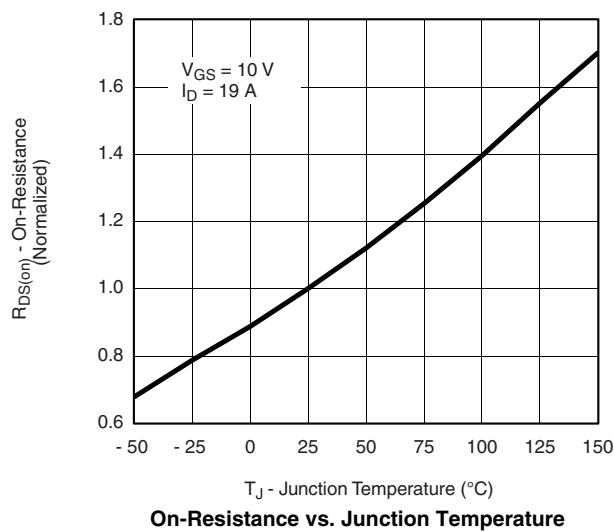
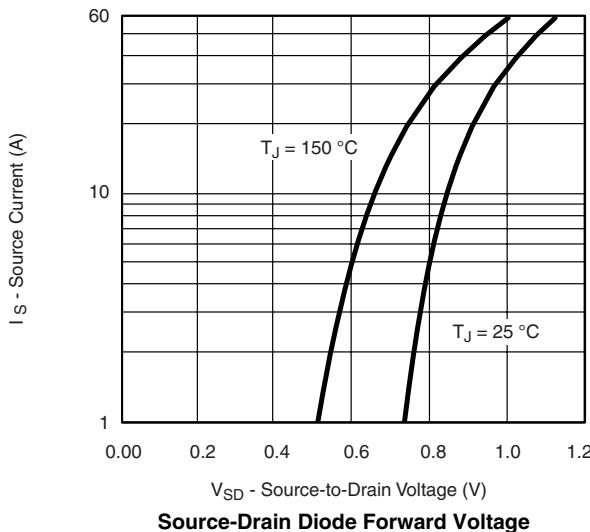
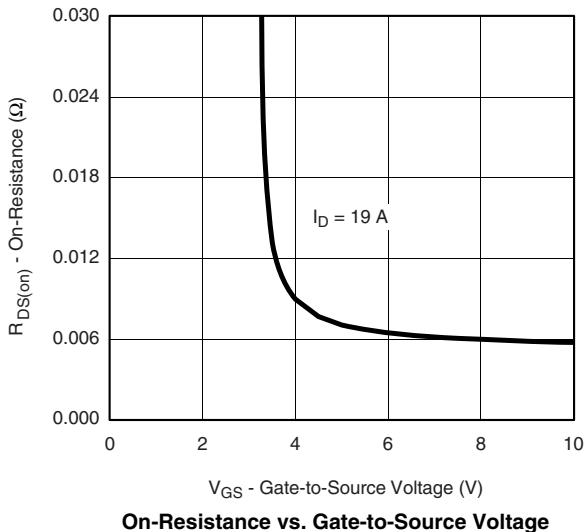
Notes:

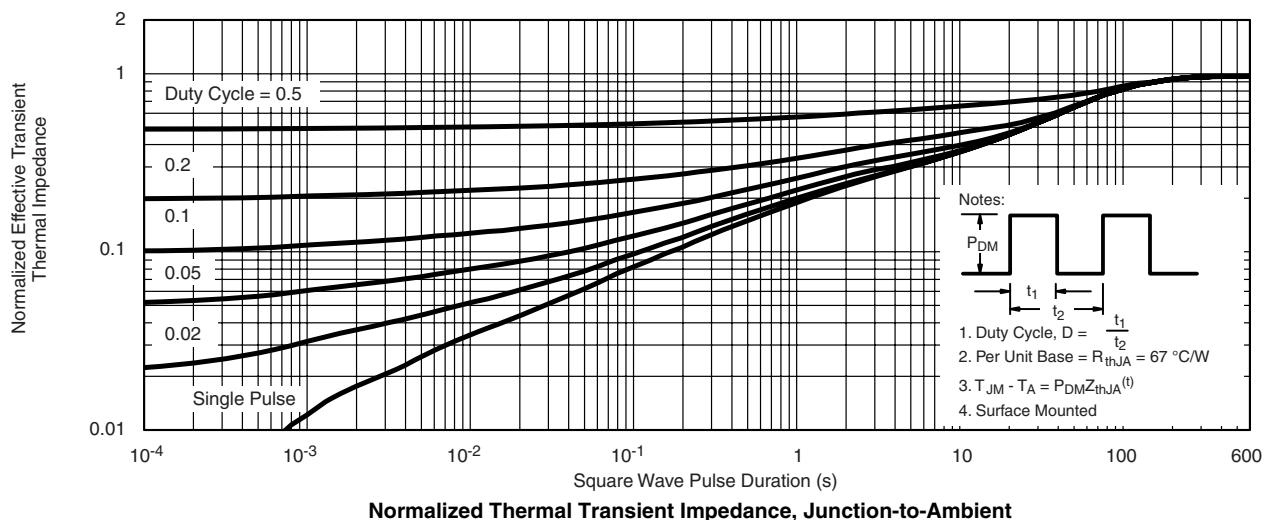
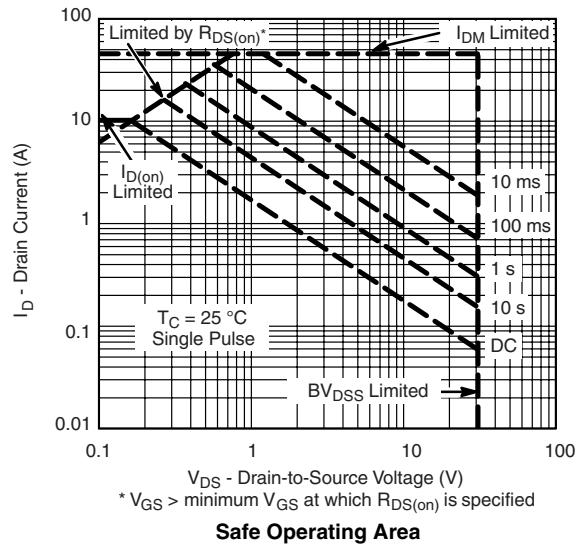
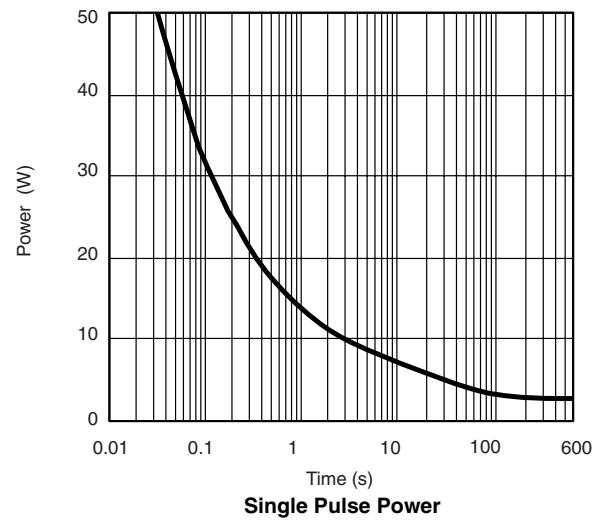
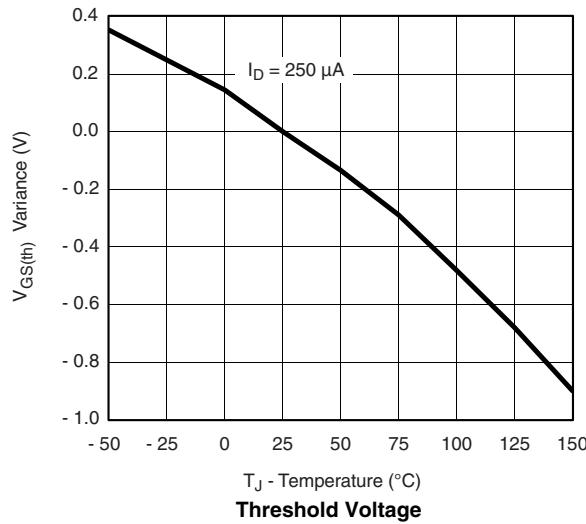
a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$.

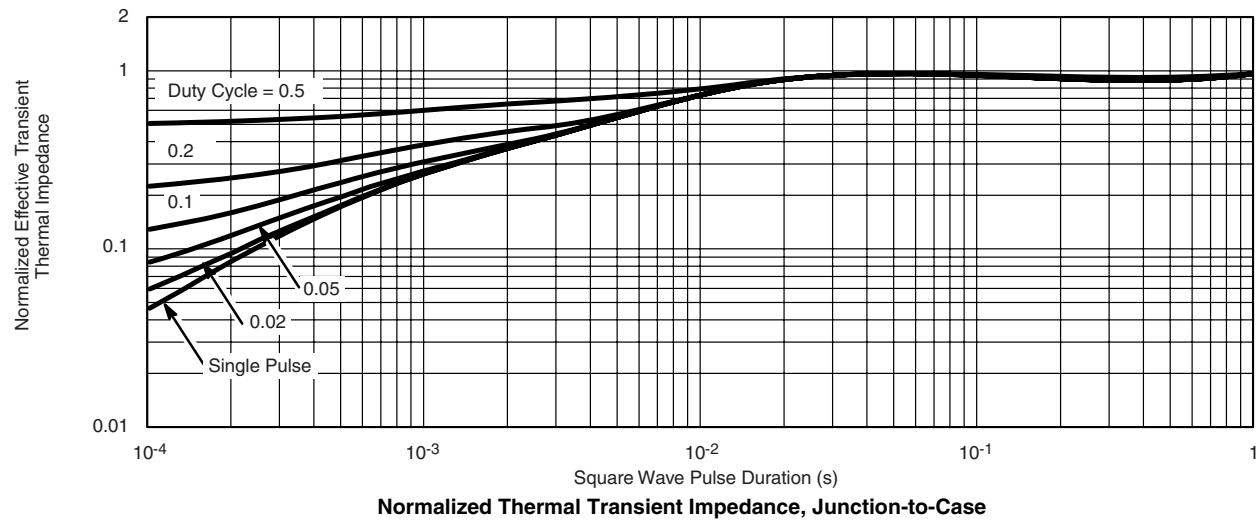
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25°C , unless otherwise noted


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


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